

L Number	Hits	Search Text	DB	Time stamp
1	84	((field adj effect) or FET?) same ((aluminum adj nitride) or AlN)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/29 11:07
2	75	((field adj effect) or FET?) same ((aluminum adj nitride) or AlN)) and @ad<20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/29 10:57
3	3	((field adj effect) or FET?) same ((aluminum adj nitride) or AlN)) same passivat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/29 10:37
4	2	((field adj effect) or FET?) same ((aluminum adj nitride) or AlN)) same passivat\$3) and @ad<20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/29 10:58
5	9	((field adj effect) or FET?) same ((aluminum adj nitride) or AlN)) same (heterojunction or HFET?)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/29 11:02
6	8	((field adj effect) or FET?) same ((aluminum adj nitride) or AlN)) same (heterojunction or HFET?)) and @ad<20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/29 11:03
7	17	((field adj effect) or FET?) same ((aluminum adj nitride) or AlN)) and (heterojunction or HFET?)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/29 11:02
8	8	((field adj effect) or FET?) same ((aluminum adj nitride) or AlN)) and (heterojunction or HFET?)) not (((field adj effect) or FET?) same ((aluminum adj nitride) or AlN)) same (heterojunction or HFET?))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/29 11:02
9	8	((field adj effect) or FET?) same ((aluminum adj nitride) or AlN)) and (heterojunction or HFET?)) not (((field adj effect) or FET?) same ((aluminum adj nitride) or AlN)) same (heterojunction or HFET?)) and @ad<20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/29 11:08
10	121	passivat\$3 with ((aluminum adj nitride) or AlN)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/29 11:08
11	112	(passivat\$3 with ((aluminum adj nitride) or AlN)) and @ad<20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/29 11:16
12	5	(passivat\$3 with ((aluminum adj nitride) or AlN)) and (heterojunction or HFET?)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/29 11:30

13	3	((passivat\$3 with ((aluminum adj nitride) or AlN)) and (heterojunction or HFET?)) and @ad<20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/29 11:18
14	7	(passivat\$3 with ((aluminum adj nitride) or AlN)) and (FET?)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/29 11:18
15	6	((passivat\$3 with ((aluminum adj nitride) or AlN)) and (FET?)) and @ad<20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/29 11:30
16	28	(passivat\$3 near5 surface) with (heterojunction or HFET?)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/29 11:30
17	26	((passivat\$3 near5 surface) with (heterojunction or HFET?)) and @ad<20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/29 11:31